

## CLEAN VERSION OF CLAIMS

117. (Cancelled) A device comprising:
  - at least one vertically oriented carbon nanotube embedded in a silicon-based substrate without protruding beyond the said substrate in air.
118. (Cancelled) A device of claim 117, wherein the said substrate material comprises a member of the class consisting of undoped silicon, doped silicon, crystalline silicon, polysilicon, silicon nitride, undoped silicon dioxide, and doped silicon dioxide.
119. (Cancelled) A device of claim 117, wherein the said carbon nanotube is fabricated directly within a template in the said substrate.
120. (Cancelled) A device of claim 117, wherein said vertically oriented carbon nanotube is at least partially electrically isolated from the said substrate.
121. (Previously Presented) A device comprising:
  - at least one vertically oriented carbon nanotube;
  - at least one horizontal conductive layer, wherein the said horizontal conductive layer is electrically coupled to said vertically oriented carbon nanotube; and
  - wherein the said horizontal conductive layer includes patterned lines.
122. (Cancelled)
123. (Cancelled).
124. (Previously Presented) A device of claim 121, wherein said carbon nanotube is conductive.
125. (Previously Presented) A device of claim 121, wherein said horizontal conductive layer material comprises a member of the class consisting of aluminum, copper, tungsten, titanium, nickel, chromium, and their alloys.

126. (Cancelled) A device comprising:

at least one vertically aligned carbon nanotube, wherein said vertically aligned carbon nanotube is fabricated within vertically aligned holes within a substrate material;

at least one horizontal conducting interconnect, wherein said interconnect is electrically coupled to said vertically aligned carbon nanotube; and

wherein a plurality of said vertically aligned carbon nanotubes form a pattern in the said substrate material.

127. (Cancelled) A device of claim 126, wherein said substrate material comprises a member of the class consisting of silicon, silicon nitride, silicon dioxide, aluminum, alumina, and gallium arsenide.

128. (Cancelled)

129. (Cancelled) A device comprising:

a first electronic device having at least one logic device;

a second electronic device having at least one logic device; and

at least one carbon nanotube, wherein the said carbon nanotube is electrically coupled to said first electronic device and said second electronic device.

130. (Cancelled) A device of claim 129, wherein said carbon nanotube is a vertically oriented carbon nanotube.

131. (Cancelled) A device of claim 129, wherein said carbon nanotube is a horizontally oriented carbon nanotube.

132. (Cancelled)

133. (Cancelled) A device having plurality of carbon nanotubes in a substrate comprising:

a first carbon nanotube;

a second carbon nanotube; and

wherein said first carbon nanotube crosses path with said second carbon nanotube at a point such that said first carbon nanotube and said second carbon nanotube are electrically coupled.

134. (Previously Presented) A device comprising:

at least one vertically oriented carbon nanotube embedded in a substrate, wherein the said nanotube is protruding from the said substrate;

at least one horizontal conductive layer, wherein the said horizontal conductive layer is electrically coupled to said vertically oriented carbon nanotube; and

wherein the said horizontal conductive layer includes patterned lines.

135. (Cancelled) A device comprising:

at least one vertically oriented carbon nanotube, wherein said carbon nanotube is conductive; and

at least one horizontal conductive layer, wherein the said horizontal conductive layer is electrically coupled to said vertically oriented carbon nanotube.

136. (Cancelled) A device of claim 135, wherein the said horizontal conductive layer includes a blanket deposited film.